## **BGU7003**

# Wideband silicon germanium low-noise amplifier MMIC Rev. 02 — 22 June 2010 Product det

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

The BGU7003 MMIC is a wideband amplifier in SiGe:C technology for high speed, low-noise applications in a plastic, leadless 6 pin, extremely thin small outline SOT891 package.

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

#### 1.2 Features

- Low noise high gain microwave MMIC
- Applicable between 40 MHz and 6 GHz
- Integrated temperature stabilized bias for easy design
- Bias current configurable with external resistor
- Noise figure NF = 0.80 dB at 1.575 GHz
- Insertion power gain = 18.3 dB at 1.575 GHz
- 110 GHz transit frequency SiGe:C technology
- Power-down mode current consumption < 1 μA
- Optimized performance at low 5 mA supply current
- ESD protection > 1 kV Human Body Model (HBM) on all pins

#### 1.3 Applications

- GPS
- Satellite radio
- Low-noise amplifiers for microwave communications systems
- WLAN and CDMA applications
- Analog / digital cordless applications



#### Wideband silicon germanium low-noise amplifier MMIC

#### 1.4 Quick reference data

Table 1. Quick reference data

 $T_{amb}$  = 25 °C;  $V_{CC}$  = 2.5 V;  $I_{CC(tot)}$  = 5.0 mA;  $V_{ENABLE}$   $\geq$  0.7 V; f = 1575 MHz;  $Z_S$  =  $Z_L$  = 50  $\Omega$  (input and output matched to 50  $\Omega$ ) unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{CC}$	supply voltage	RF input AC coupled		2.2	-	2.85	V
I <sub>CC(tot)</sub>	total supply current	configurable with external resistor	[1]	3	-	15	mΑ
T <sub>amb</sub>	ambient temperature			-40	+25	+85	°C
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> ≤ 103 °C	[2]	-	-	70	mW
$ s_{21} ^2$	Insertion power gain			-	18.3	-	dB
NF	noise figure			-	0.80	-	dB
P <sub>i(1dB)</sub>	input power at 1 dB gain compression			-	-20.1	-	dBm
IP3 <sub>I</sub>	input third-order intercept point	jammers at $f_1 = f + 138$ MHz and $f_2 = f + 276$ MHz		-	-0.2	-	dBm

<sup>[1]</sup>  $I_{CC(tot)} = I_{CC} + I_{RF\_OUT} + I_{R\_BIAS}$ .

## 2. Pinning information

Table 2.	Pinning

10010 21	9		
Pin	Description	Simplified outline	Graphic symbol
1	R_BIAS		
2	RF_IN	1 2 3	5 6
3	GND		2———4
4	RF_OUT		
5	ENABLE		1 3 sym128
6	V <sub>CC</sub>	6 5 4 bottom view	,

## 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BGU7003	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891			

## 4. Marking

Table 4. Marking codes

Type number	Marking code
BGU7003	B3

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<sup>[2]</sup>  $T_{sp}$  is the temperature at the solder point of the ground lead.

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## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CC}$	supply voltage	RF input AC coupled		-	3.0	V
I <sub>CC(tot)</sub>	total supply current	configurable with external resistor		-	25	mΑ
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> ≤ 103 °C	[1]	-	70	mW
T <sub>stg</sub>	storage temperature			-65	+150	°C
Tj	junction temperature			-	150	°C

<sup>[1]</sup>  $T_{sp}$  is the temperature at the solder point of the ground lead.

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		235	K/W

## 7. Characteristics

Table 7. Characteristics

 $T_{amb}$  = 25 °C;  $V_{CC}$  = 2.5 V;  $I_{CC(tot)}$  = 5.0 mA;  $V_{ENABLE}$   $\geq$  0.7 V unless otherwise specified. All measurements done on characterization board without matching, de-embedded up to the pins.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{CC}$	supply voltage	RF input AC coupled		2.2	-	2.85	V
I <sub>CC(tot)</sub>	total supply current	configurable with external resistor	[1]	3	-	15	mΑ
		$V_{\text{ENABLE}} \leq 0.4 \text{ V}$	[1]	-	-	0.001	mΑ
T <sub>amb</sub>	ambient temperature			-40	+25	+85	°C
$ s_{21} ^2$	insertion power gain	T <sub>amb</sub> = 25 °C					
		f = 1.575 GHz		16.0	17.5	-	dB
		f = 2.4 GHz	[2]	14.0	15.2	-	dB
		f = 5.8 GHz	[2]	10.0	11.4	-	dB
		$-40  ^{\circ}\text{C} \le T_{amb} \le 85  ^{\circ}\text{C}$					
		f = 1.575 GHz	[2]	15.0	17.5	-	dB
		f = 2.4 GHz	[2]	13.0	15.2	-	dB
		f = 5.8 GHz	[2]	9.0	11.4	-	dB
MSG	maximum stable gain	f = 1.575 GHz		-	20.5	-	dB
		f = 2.4 GHz		-	17.8	-	dB
		f = 5.8 GHz		-	15.4	-	dB
$NF_{min}$	minimum noise figure	f = 1.575 GHz		-	0.70	-	dB
		f = 2.4 GHz		-	0.80	-	dB
		f = 5.8 GHz		-	1.5	-	dB

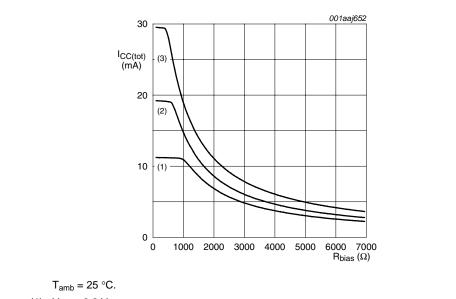
<sup>[1]</sup>  $I_{CC(tot)} = I_{CC} + I_{RF\_OUT} + I_{R\_BIAS}$ .

<sup>[2]</sup> Guaranteed by design and characterization.

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Table 8. ENABLE (pin 5)  $-40 \, ^{\circ}\text{C} \le T_{amb} \le +85 \, ^{\circ}\text{C}$ 

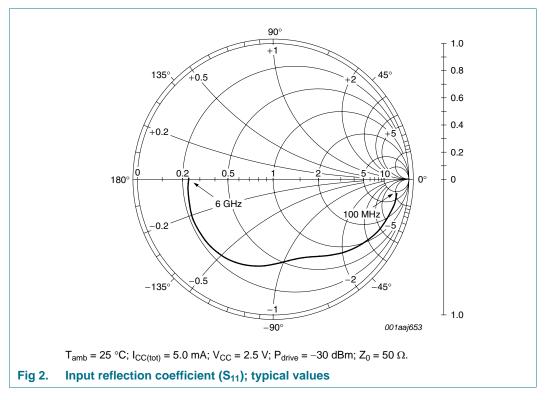
V <sub>ENABLE</sub> (V)	State
≤ 0.4	OFF
≥ 0.7	ON

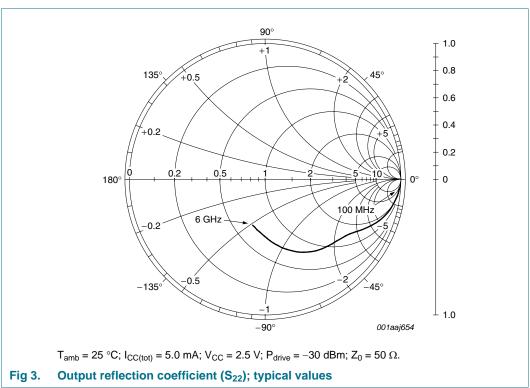


- (1)  $V_{CC} = 2.2 \text{ V}$
- (2)  $V_{CC} = 2.5 \text{ V}$
- (3)  $V_{CC} = 2.85 \text{ V}$

Fig 1. Total supply current as a function of bias resistor; typical values

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#### Wideband silicon germanium low-noise amplifier MMIC

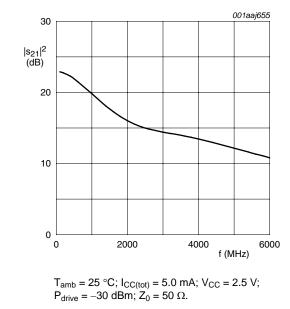


Fig 4. Insertion power gain  $(|s_{21}|^2)$  as a function of frequency; typical values

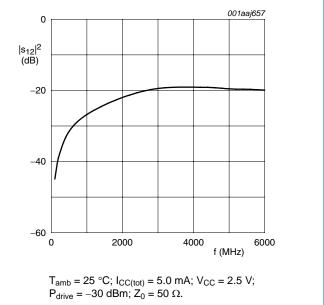


Fig 5. Isolation ( $|s_{12}|^2$ ) as a function of frequency; typical values

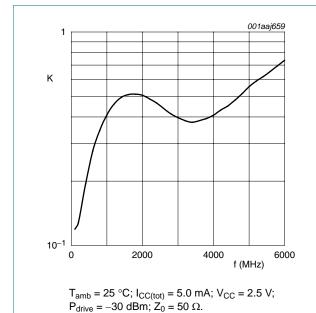


Fig 6. Rollet's stability factor as a function of frequency; typical values

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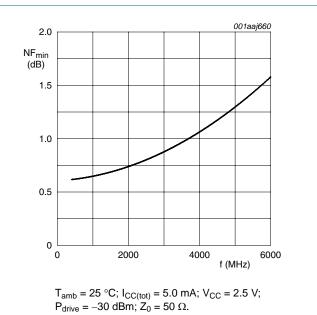
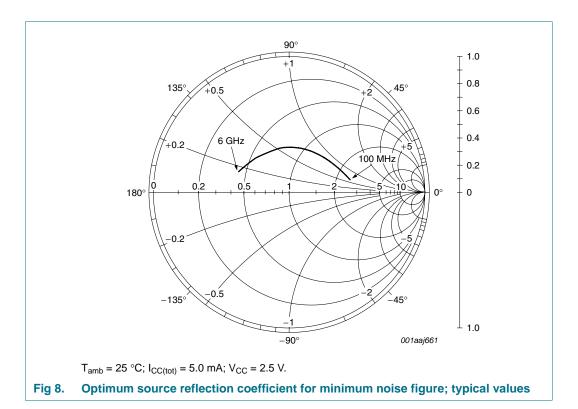
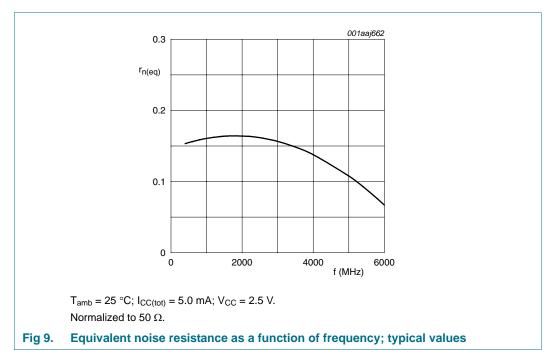


Fig 7. Minimum noise figure as a function of frequency; typical values

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## **Application information GPS LNA**

Other applications available. Please contact your local sales representative for more information. Application note(s) available on the NXP website.

#### **Application circuit**

In Figure 10 the application diagram as supplied on the evaluation board is given.

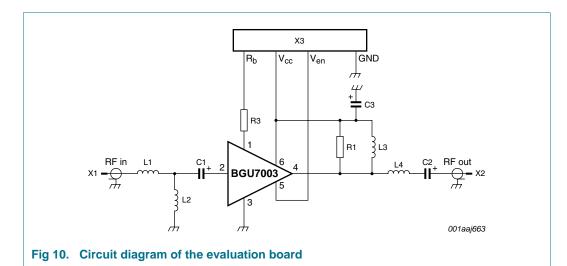


Table 9. List of components For circuit, see Figure 10.

Component	Description	Value		Supplier name/type	Remarks
C1, C2	capacitor	100 pF	[1]	MurataGRM1555	DC blocking
C3	capacitor	180 pF	[1]	MurataGRM1555	decoupling
L1	inductor	2.7 nH	[1]	Murata/LQW15A high quality factor, low series resistance	input matching
L2	inductor	33 nH	[1]	Murata/LQW15A high quality factor, low series resistance	input matching
L3	inductor	3.9 nH	[1]	Murata/LQG15HS	output matching / DC shunt
L4	inductor	4.7 nH	[1]	Murata/LQG15HS	output matching
R1	resistor	180 Ω	[1]		
R2	resistor	0 Ω	[1]		bridge
R3	resistor	3300 $\Omega$	[1]		bias setting
X1, X2	SMA RF connector	-		Johnson, end launch SMA 142-0701-841	RF input / RF output
Х3	DC header	-		Molex, PCB header, right angle, 1 row, 4 way 90121-0764	bias connector

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<sup>[1]</sup> all capacitors, inductors and resistors have 0402 footprint.

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#### 8.2 Application board layout

Figure 11 shows the board layout with component identifications.

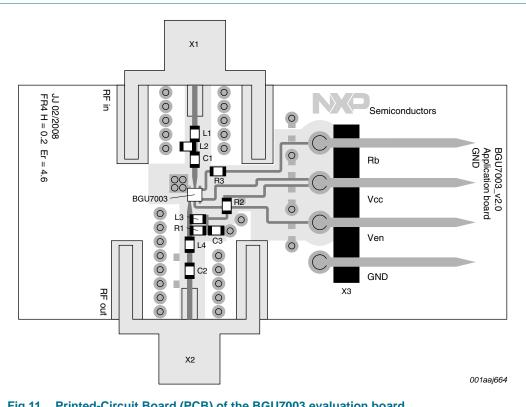
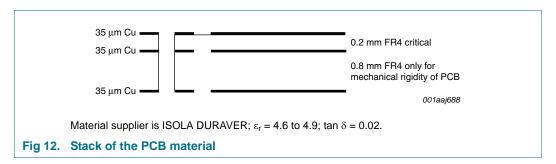


Fig 11. Printed-Circuit Board (PCB) of the BGU7003 evaluation board

#### 8.3 Printed-Circuit Board

The material that has been used for the evaluation board is FR4 using the stack shown in Figure 12.



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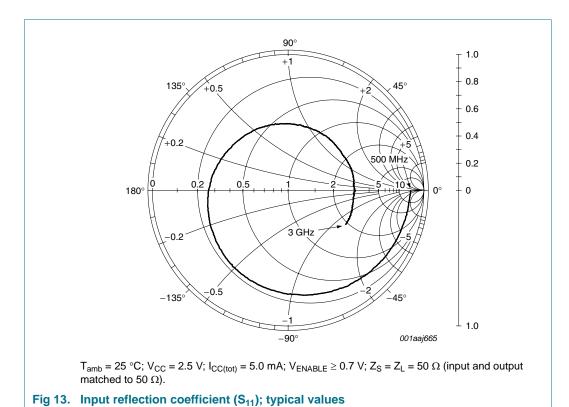
#### Wideband silicon germanium low-noise amplifier MMIC

#### 8.4 GPS evaluation board

#### Table 10. GPS application characteristics

 $T_{amb}$  = 25 °C;  $V_{CC}$  = 2.5 V;  $I_{CC(tot)}$  = 5.0 mA; f = 1.575 GHz;  $V_{ENABLE} \ge 0.7$  V;  $Z_{S}$  =  $Z_{L}$  = 50  $\Omega$  (input and output matched to 50  $\Omega$ ) unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$ s_{21} ^2$	Insertion power gain		-	18.3	-	dB
$ s_{11} ^2$	input return loss		-	-5.4	-	dB
$ s_{22} ^2$	output return loss		-	-19.5	-	dB
$ s_{12} ^2$	isolation		-	-24.6	-	dB
NF	noise figure		-	0.80	-	dB
$P_{i(1dB)}$	input power at 1 dB gain compression		-	-20.1	-	dBm
P <sub>L(1dB)</sub>	output power at 1 dB gain compression		-	-2.8	-	dBm
IP3 <sub>I</sub>	input third-order intercept point	jammers at $f_1 = f + 138$ MHz and $f_2 = f + 276$ MHz	-	-0.2	-	dBm
		$f_1 = f + 5 \text{ MHz}; f_2 = f + 10 \text{ MHz}$	-	-5.2	-	dBm



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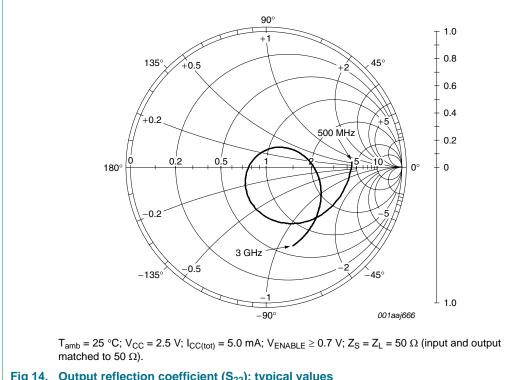
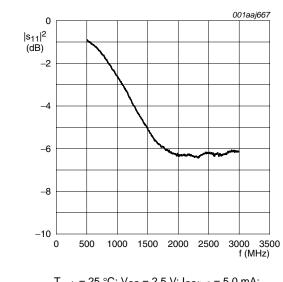
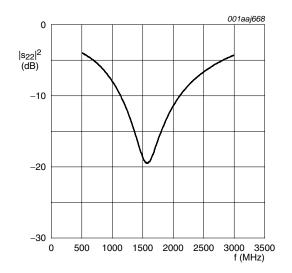


Fig 14. Output reflection coefficient (S<sub>22</sub>); typical values



 $T_{amb} = 25 \, ^{\circ}C; \, V_{CC} = 2.5 \, V; \, I_{CC(tot)} = 5.0 \, mA;$  $V_{ENABLE} \geq 0.7$  V;  $Z_{S}$  =  $Z_{L}$  = 50  $\Omega$  (input and output matched to 50  $\Omega$ ).

Fig 15. Input return loss ( $|s_{11}|^2$ ) as a function of frequency; typical values

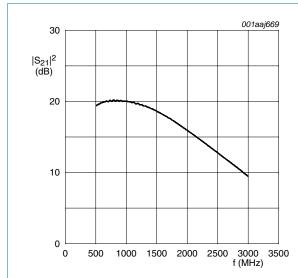


 $T_{amb} = 25 \, ^{\circ}C; \, V_{CC} = 2.5 \, V; \, I_{CC(tot)} = 5.0 \, mA;$  $V_{ENABLE} \geq 0.7$  V;  $Z_{S}$  =  $Z_{L}$  = 50  $\Omega$  (input and output matched to 50  $\Omega$ ).

Fig 16. Output return loss ( $|s_{22}|^2$ ) as a function of frequency; typical values

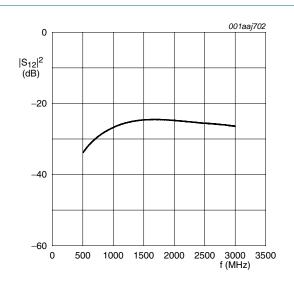
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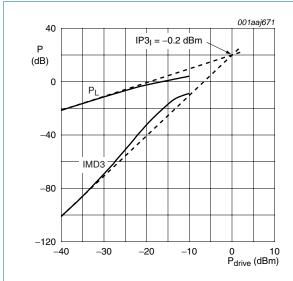
 $T_{amb}$  = 25 °C;  $V_{CC}$  = 2.5 V;  $I_{CC(tot)}$  = 5.0 mA;  $V_{ENABLE} \ge 0.7 \text{ V}$ ;  $Z_S = Z_L = 50 \Omega$  (input and output matched to 50  $\Omega$ ).

Fig 17. Insertion power gain  $(|s_{21}|^2)$  as a function of frequency; typical values



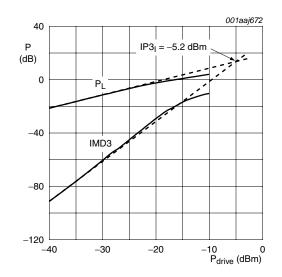
 $T_{amb}$  = 25 °C;  $V_{CC}$  = 2.5 V;  $I_{CC(tot)}$  = 5.0 mA;  $V_{ENABLE} \ge 0.7 \text{ V}$ ;  $Z_S = Z_L = 50 \Omega$  (input and output matched to 50  $\Omega$ ).

Fig 18. Reverse Isolation ( $|s_{12}|^2$ ) as a function of frequency; typical values



 $T_{amb}$  = 25 °C;  $V_{CC}$  = 2.5 V;  $I_{CC(tot)}$  = 5.0 mA; f = 1.575 GHz;  $f_1 = f + 138 \text{ MHz}$ ;  $f_2 = f + 276 \text{ MHz}$ ;  $V_{ENABLE} \ge 0.7 \text{ V}$ ;  $Z_S = Z_L = 50 \Omega$  (input and output matched to 50  $\Omega$ )

Fig 19. Load power and third order intermodulation distortion as function of drive power; typical values



 $T_{amb} = 25 \text{ °C}; V_{CC} = 2.5 \text{ V}; I_{CC(tot)} = 5.0 \text{ mA};$ f = 1.575 GHz;  $f_1 = f + 5 \text{ MHz}$ ;  $f_2 = f + 10 \text{ MHz}$ ;  $V_{ENABLE} \ge 0.7 \text{ V}$ ;  $Z_S = Z_L = 50 \Omega$  (input and output matched to 50  $\Omega$ )

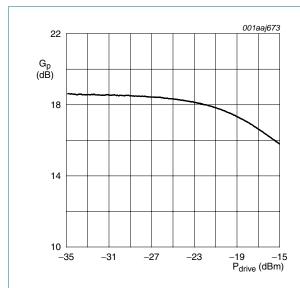
Fig 20. Load power and third order intermodulation distortion as function of drive power; typical values

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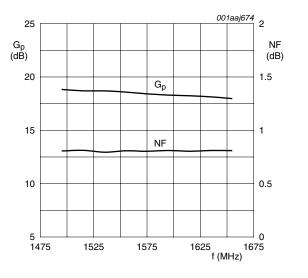
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 $T_{amb}$  = 25 °C;  $V_{CC}$  = 2.5 V;  $I_{CC(tot)}$  = 5.0 mA; f = 1.575 GHz;  $V_{ENABLE} \geq 0.7$  V;  $Z_S$  =  $Z_L$  = 50  $\Omega$  (input and output matched to 50  $\Omega$ ).

Fig 21. Power gain as a function of drive power; typical values



$$\begin{split} &T_{amb} = 25~^{\circ}C;~V_{CC} = 2.5~V;~I_{CC(tot)} = 5.0~mA;\\ &V_{ENABLE} \geq 0.7~V;~Z_{S} = Z_{L} = 50~\Omega~(input~and~output~) \end{split}$$
matched to 50  $\Omega$ ).

Fig 22. Power gain and noise figure as function of frequency; typical values

## 9. Package outline

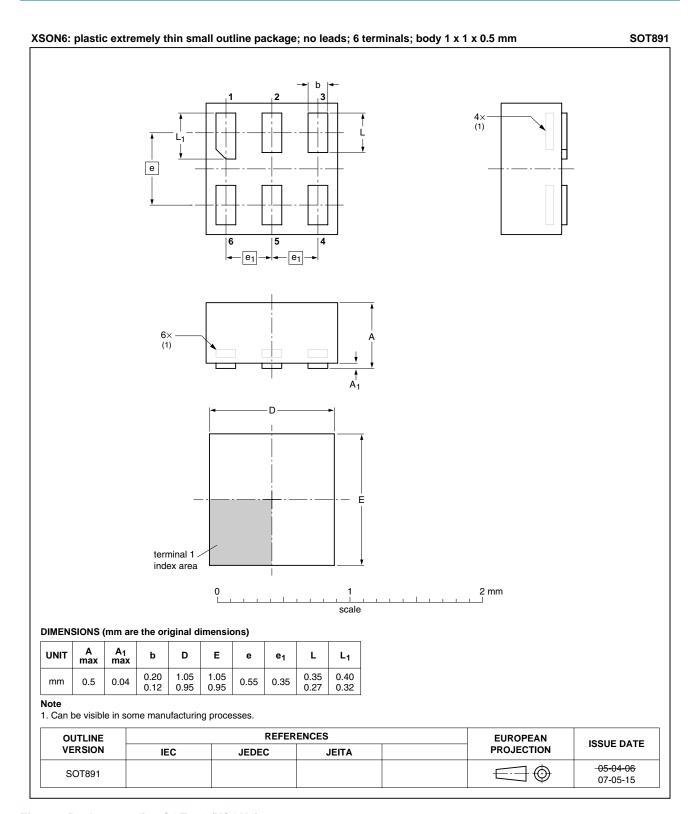
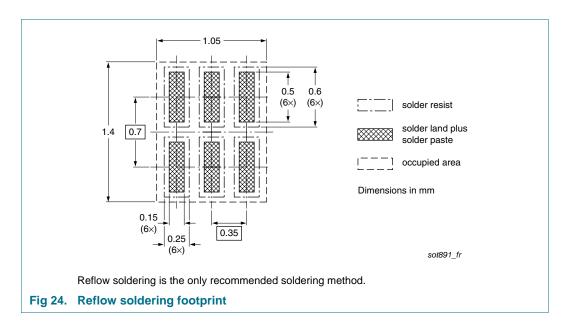


Fig 23. Package outline SOT891 (XSON6)

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#### Wideband silicon germanium low-noise amplifier MMIC

## 10. Soldering



## 11. Abbreviations

Table 11. Abbreviations

Acronym	Description
AC	Alternating Current
CDMA	Code Division Multiple Access
DC	Direct Current
FR4	Flame Retardant 4
GPS	Global Positioning System
LNA	Low-Noise Amplifier
MMIC	Monolithic Microwave Integrated Circuit
RF	Radio Frequency
SiGe:C	Silicon Germanium Carbon
SMA	SubMiniature version A
WLAN	Wireless Local Area Network

## 12. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU7003 v.2	20100622	Product data sheet	-	BGU7003 v.1
Modifications:	<ul> <li>Legal inform</li> </ul>	ation updated.		
BGU7003 v.1	20090302	Product data sheet	-	-

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#### Wideband silicon germanium low-noise amplifier MMIC

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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#### Wideband silicon germanium low-noise amplifier MMIC

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#### Wideband silicon germanium low-noise amplifier MMIC

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